

Tailoring the Electrical properties of Multilayer MoS₂ Transistors by Ultraviolet Light Irradiation

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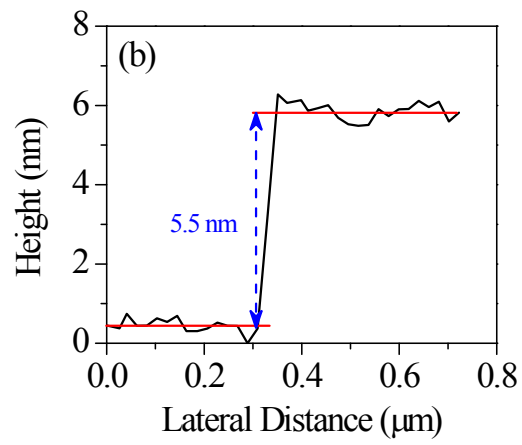
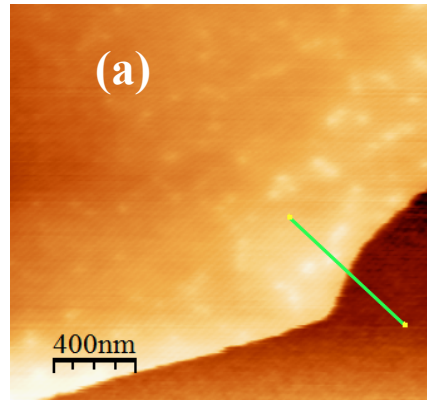


Figure S1 (a)AFM image of ML MoS₂ and (b) corresponding height profile.

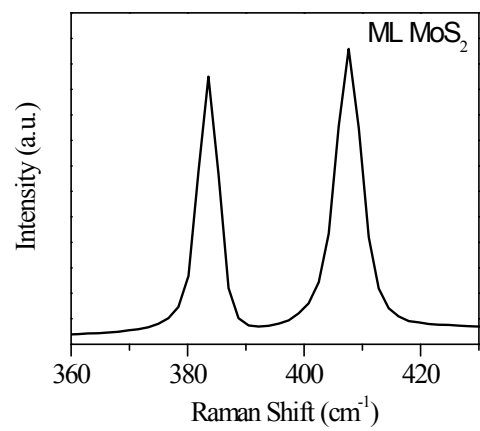


Figure S2- Raman spectra of pristine ML MoS₂.

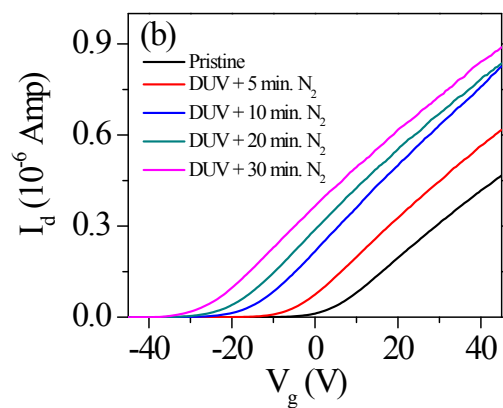
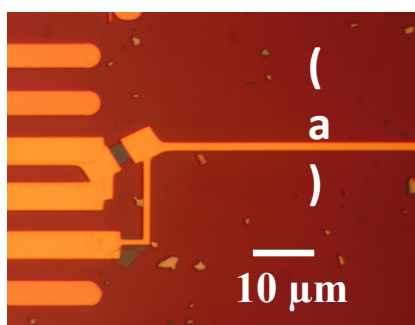


Figure S3- (a) Optical image of mechanically fabricated ML MoS₂ FET device. (b) The I_D - V_{bg} characteristics with different exposure time of N₂ gas under DUV light for ML MoS₂ transistors.

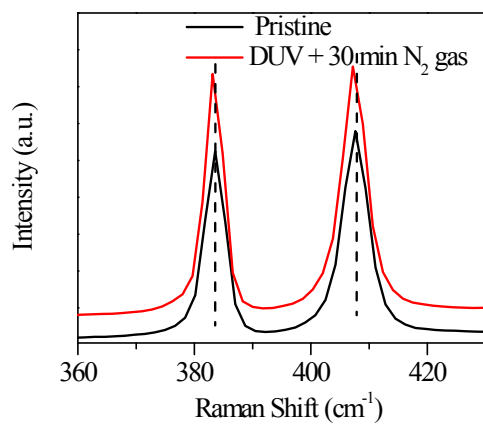


Figure S4- Raman spectra of pristine and 30 minutes N₂ gas expose ML MoS₂ under DUV light